

# **isc Silicon PNP Power Transistor**

## **DESCRIPTION**

- DC Current Gain-
  - : h<sub>FE</sub>= 40(Min)@ I<sub>C</sub>= -0.15A
- · Collector-Emitter Sustaining Voltage -
  - : V<sub>CEO(SUS)</sub>= -60V(Min)
- Complement to type BD137
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

 Designed for use as audio amplifiers and drivers utilizing complementary or quasi complementary circuits.

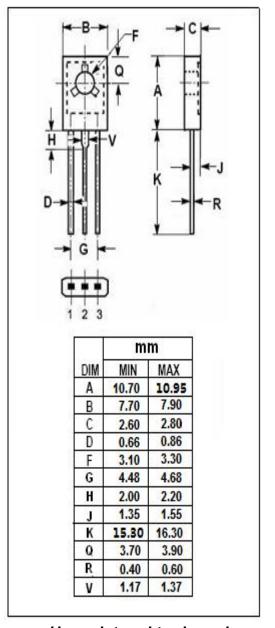
# 3 TO-126 package

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)						
SYMBOL	PARAMETER VALUE		UNIT			
$V_{\text{CBO}}$	Collector-Base Voltage	-60	V			
Vceo	Collector-Emitter Voltage	-60	V			
V <sub>EBO</sub>	Emitter-Base Voltage -5		V			
Ic	Collector Current-Continuous -		А			
I <sub>B</sub>	Base Current-Continuous -0.5		А			
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.25	W			
	Collector Power Dissipation @ T <sub>C</sub> =25 °C	12.5				
TJ	Junction Temperature 150		$^{\circ}$			
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C			

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	10	°C/W	
R <sub>th j-a</sub>	-a Thermal Resistance,Junction to Ambient		°C/W	



isc website: www.iscsemi.com

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# isc Silicon PNP Power Transistor

**BD138** 

# **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = -30mA ; I <sub>B</sub> =0	-60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -0.5A; I <sub>B</sub> = -50mA			-0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V			-1.0	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -30V; I <sub>E</sub> = 0 V <sub>CB</sub> = -30V; I <sub>E</sub> = 0,T <sub>C</sub> =125°C			-0.1 -10	μА
І <sub>ЕВО</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> =0			-10	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -5mA ; V <sub>CE</sub> = -2V	25			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -2V	25			
h <sub>FE-3</sub>	DC Current Gain	Ic= -0.15A; Vc= -2V	40		250	



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